Welcome to E-XFL.COM

What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM7®
Core Size	32-Bit Single-Core
Speed	60MHz
Connectivity	CANbus, I²C, SPI, SSI, SSP, UART/USART
Peripherals	DMA, PWM, WDT
Number of I/O	38
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	3V ~ 5.5V
Data Converters	A/D 11x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	-
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/str752fr1t7

3 Introduction

This Datasheet contains the description of the STR750F family features, pinout, Electrical Characteristics, Mechanical Data and Ordering information.

For complete information on the Microcontroller memory, registers and peripherals. Please refer to the STR750F Reference Manual.

For information on the ARM7TDMI-S core please refer to the ARM7TDMI-S Technical Reference Manual available from Arm Ltd.

For information on programming, erasing and protection of the internal Flash memory please refer to the STR7 Flash Programming Reference Manual

For information on third-party development tools, please refer to the http://www.st.com/mcu website.

3.1 Functional description

The STR750F family includes devices in 2 package sizes: 64-pin and 100-pin. Both types have the following common features:

ARM7TDMI-S™ core with embedded Flash & RAM

STR750F family has an embedded ARM core and is therefore compatible with all ARM tools and software. It combines the high performance ARM7TDMI-S™ CPU with an extensive range of peripheral functions and enhanced I/O capabilities. All devices have on-chip high-speed single voltage FLASH memory and high-speed RAM.

Figure 1 shows the general block diagram of the device family.

Embedded Flash memory

Up to 256 KBytes of embedded Flash is available in Bank 0 for storing programs and data. An additional Bank 1 provides 16 Kbytes of RWW (Read While Write) memory allowing it to be erased/programmed on-the-fly. This partitioning feature is ideal for storing application parameters.

- When configured in burst mode, access to Flash memory is performed at CPU clock speed with 0 wait states for sequential accesses and 1 wait state for random access (maximum 60 MHz).
- When not configured in burst mode, access to Flash memory is performed at CPU clock speed with 0 wait states (maximum 32 MHz)

Embedded SRAM

16 Kbytes of embedded SRAM accessed (read/write) at CPU clock speed with 0 wait states.

Enhanced interrupt controller (EIC)

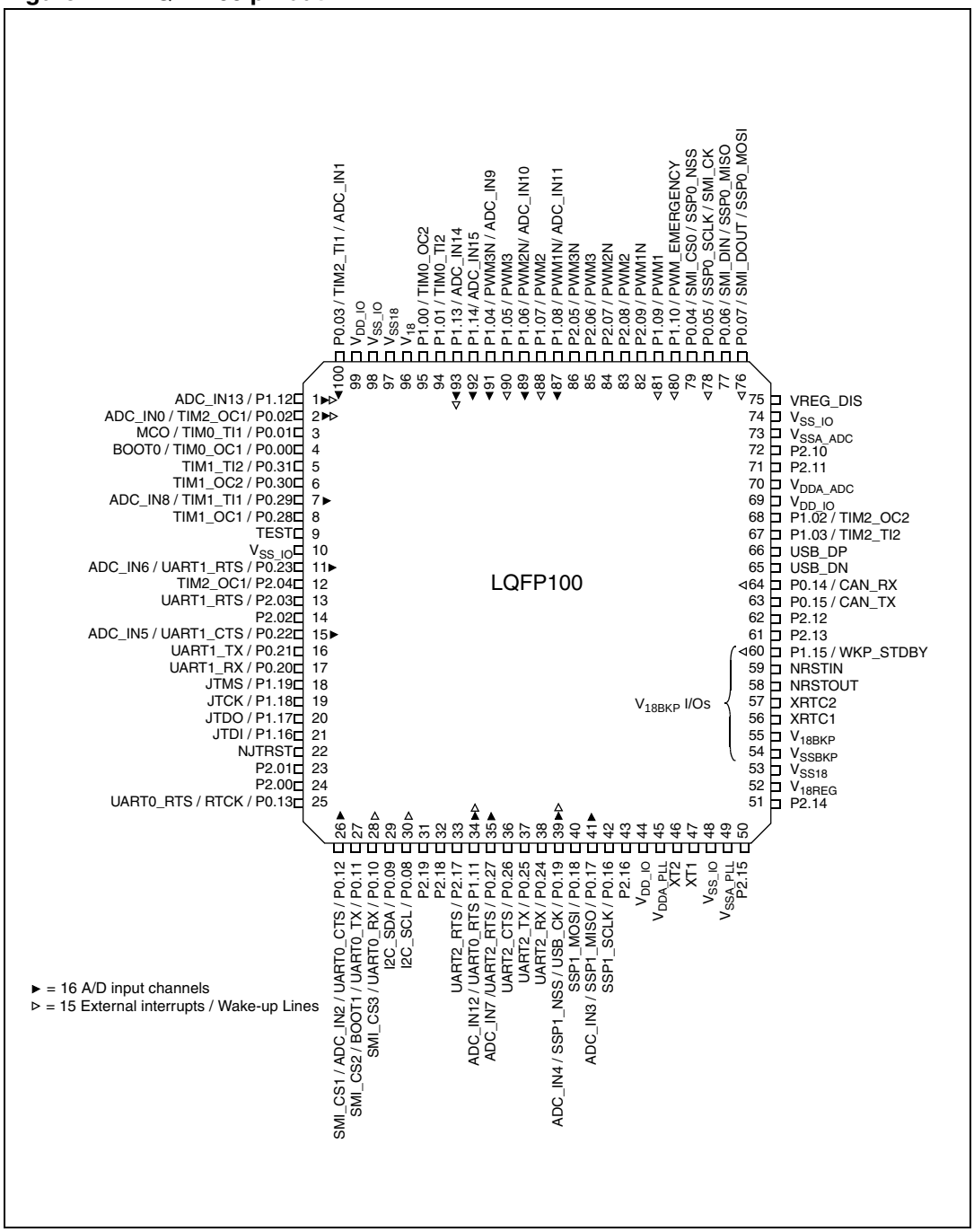
In addition to the standard ARM interrupt controller, the STR750F embeds a nested interrupt controller able to handle up to 32 vectors and 16 priority levels. This additional hardware block provides flexible interrupt management features with minimal interrupt latency.

GPIOs (general purpose input/output)

Each of the 72 GPIO pins (38 GPIOs in 64-pin devices) can be configured by software as output (push-pull or open-drain), as input (with or without pull-up or pull-down) or as Peripheral Alternate Function. Port 1.15 is an exception, it can be used as general-purpose input only or wake-up from STANDBY mode (WKP_STDBY). Most of the GPIO pins are shared with digital or analog alternate functions.

4 Pin description

Figure 2. LQFP100 pinout



Port reset state

The reset state of the I/O ports is GPIO input floating. Exceptions are P1[19:16] and P0.13 which are configured as JTAG alternate functions:

- The JTAG inputs (JTDI, JTMS and JTDI) are configured as input floating and are ready to accept JTAG sequences.
- The JTAG output JTDO is configured as floating when idle (no JTAG operation) and is configured in output push-pull only when serial JTAG data must be output.
- The JTAG output RTCK is always configured as output push-pull. It outputs '0' level during the reset phase and then outputs the JTCK input signal resynchronized 3 times by the internal AHB clock.
- The GPIO_PCx registers do not control JTAG AF selection, so the reset values of GPIO_PCx for P1[19:16] and P0. 13 are the same as other ports. Refer to the GPIO section of the STR750 Reference Manual for the register description and reset values.
- P0.11 and P0.00 are sampled by the boot logic after reset, prior to fetching the first word of user code at address 0000 0000h.
- When booting from SMI (and only in this case), the reset state of the following GPIOs is "SMI alternate function output enabled":
  - P0.07 (SMI_DOUT)
  - P0.05 (SMI_CLK)
  - P0.04 (SMI_CS0)
  - P0.06 (SMI_DIN)

  Note that the other SMI pins: SMI_CS1,2,3 (P0.12, P0.11, P0.10) are not affected.

To avoid excess power consumption, unused I/O ports must be tied to ground.

Table 6. STR750F pin description

Pin n°				Pin name	Type	Input				Output			Usable in Standby	Main function (after reset)	Alternate function	
LQFP100[1]	LFBGA100[1]	LQFP64[2]	LFBGA64[2]			Input Level	floating	pu/pd	Ext. int /Wake-up	Capability	OD [3]	PP				
1	B1	1	B1	P1.12 / ADC_IN13	I/O	T_T	**X**	X	EIT12	O8	X	X		**Port 1.12**	ADC: Analog input 13	
2	B2	2	C2	P0.02 / TIM2_OC1 / ADC_IN0	I/O	T_T	**X**	X	EIT0	O8	X	X		**Port 0.02**	TIM2: Output Compare 1[4]	ADC: Analog input 0
3	B3	3	C1	P0.01 / TIM0_TI1 / MCO	I/O	T_T	**X**	X		O8	X	X		**Port 0.01**	TIM0: Input Capture / trigger / external clock 1	Main Clock Output
4	C2	4	C3	P0.00 / TIM0_OC1 / BOOT0	I/O	T_T	**X**	X		O8	X	X		**Port 0.00 / Boot mode selection input 0**	TIM0: Output Compare 1	
5	C1			P0.31 / TIM1_TI2	I/O	T_T	**X**	X		O2	X	X		**Port 0.31**	TIM1: Input Capture / trigger / external clock 2	
6	D2			P0.30 / TIM1_OC2	I/O	T_T	**X**	X		O2	X	X		**Port 0.30**	TIM1: Output Compare 2	

Table 6. STR750F pin description (continued)

Pin n°				Pin name	Type	Input				Output			Usable in Standby	Main function (after reset)	Alternate function	
LQFP100(1)	LFBGA100(1)	LQFP64(2)	LFBGA64(2)			Input Level	floating	pu/pd	Ext. int /Wake-up	Capability	OD (3)	PP				
91	A4	59	A3	P1.04 / PWM3N / ADC_IN9	I/O	T_T	**X**	X		O4	X	X		**Port 1.04**	PWM: PWM3 complementary output(4)	ADC: analog input 9
92	A3			P1.14 / ADC_IN15	I/O	T_T	**X**	X		O8	X	X		**Port 1.14**	ADC: analog input 15	
93	A2			P1.13 / ADC_IN14	I/O	T_T	**X**	X	EIT13	O8	X	X		**Port 1.13**	ADC: analog input 14	
94	D5			P1.01 / TIM0_TI2	I/O	T_T	**X**	X		O2	X	X		**Port 1.01**	TIM0: Input Capture / trigger / external clock 2 (remappable to P0.05)(8)	
95	E6			P1.00 / TIM0_OC2	I/O	T_T	**X**	X		O2	X	X		**Port 1.00**	TIM0: Output compare 2 (remappable to P0.04)(8)	
96	C4	60	C4	V18	S									Stabilization for main voltage regulator. Requires external capacitors 33nF between V18 and VSS18. See *Figure 4.2*. To be connected to the 1.8V external power supply when embedded regulators are not used.		
97	D4	61	C5	VSS18	S									Ground Voltage for the main voltage regulator.		
98	D3	62	A2	VSS_IO	S									Ground Voltage for digital I/Os		
99	C3	63	B2	VDD_IO	S									Supply Voltage for digital I/Os		
100	A1	64	A1	P0.03 / TIM2_TI1 / ADC_IN1	I/O	T_T	**X**	X		O2	X	X		**Port 0.03**	TIM2: Input Capture / trigger / external clock 1	ADC: analog input 1

1. For STR755FVx part numbers, the USB pins must be left unconnected.
2. The non available pins on LQPFP64 and LFBGA64 packages are internally tied to low level.
3. None of the I/Os are True Open Drain: when configured as Open Drain, there is always a protection diode between the I/O pin and VDD_IO.
4. In the 100-pin package, this Alternate Function is duplicated on two ports. You can configure one port to use this AF, the other port is then free for general purpose I/O (GPIO), external interrupt/wake-up lines, or analog input (ADC_IN) where these functions are listed in the table.
5. It is mandatory that the NJTRST pin is reset to ground during the power-up phase. It is recommended to connect this pin to NRSTOUT pin (if available) or NRSTIN.
6. After reset, these pins are enabled as JTAG alternate function see (*Port reset state on page 16*). To use these ports as general purpose I/O (GPIO), the DBGOFF control bit in the GPIO_REMAP0R register must be set by software (in this case, debugging these I/Os via JTAG is not possible).
7. There are two different TQFP and BGA 64-pin packages: in the first one, pins 41 and 42 are mapped to USB DN/DP while for the second one, they are mapped to P0.15/CAN_TX and P0.14/CAN_RX.
8. For details on remapping these alternate functions, refer to the GPIO_REMAP0R register description.

Power supply scheme 2: Dual external 1.8V and 3.3V supply

Figure 9. Power supply scheme 2

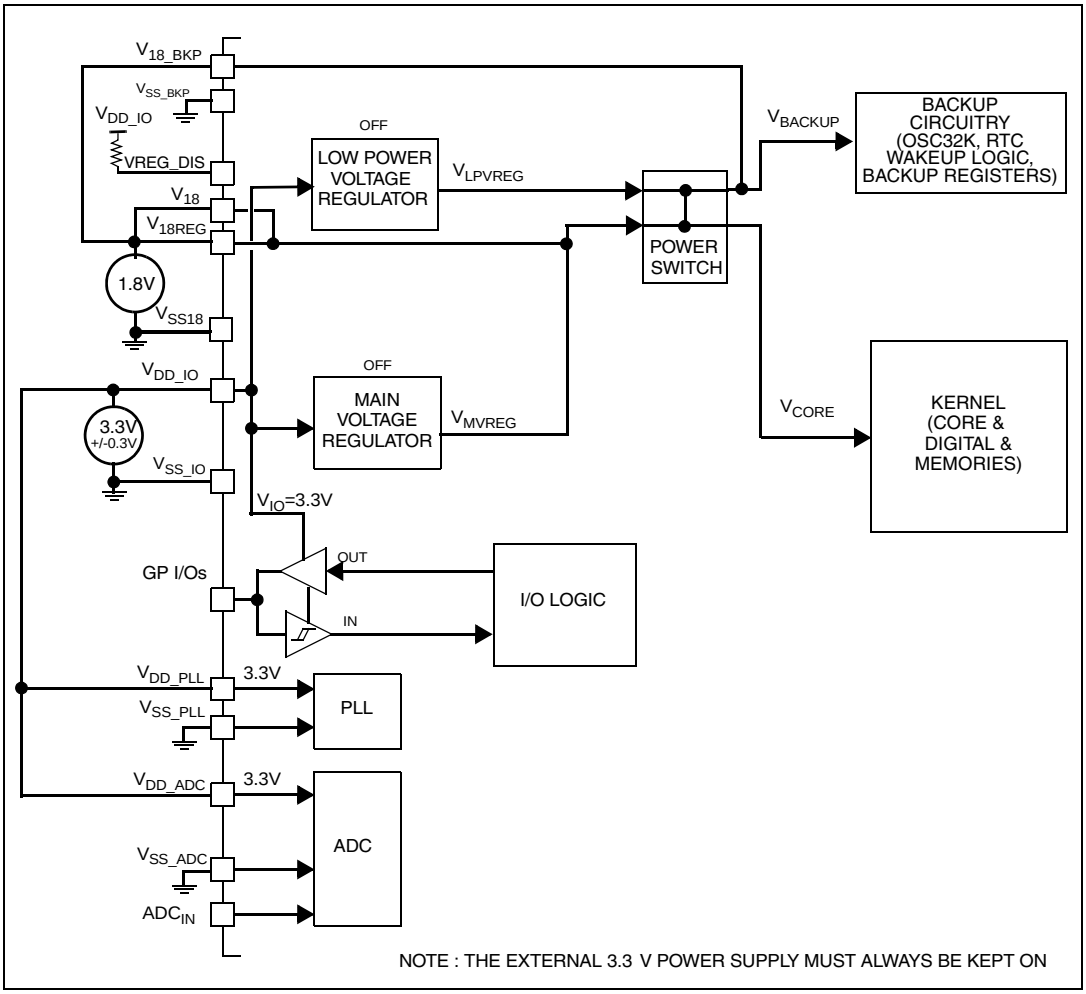


Figure 12. Power consumption measurements in power scheme 1 (regulators enabled)

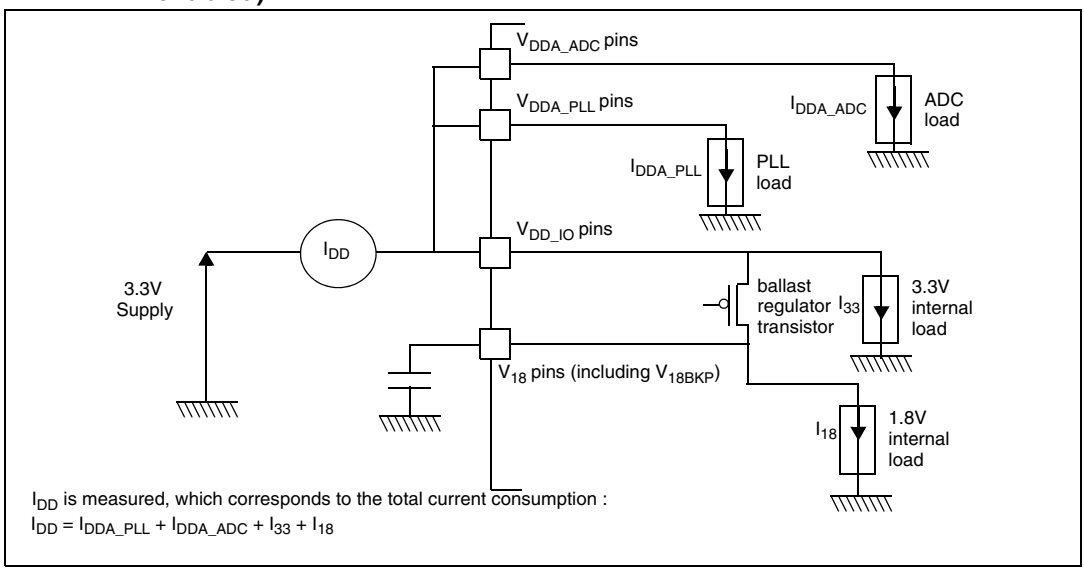
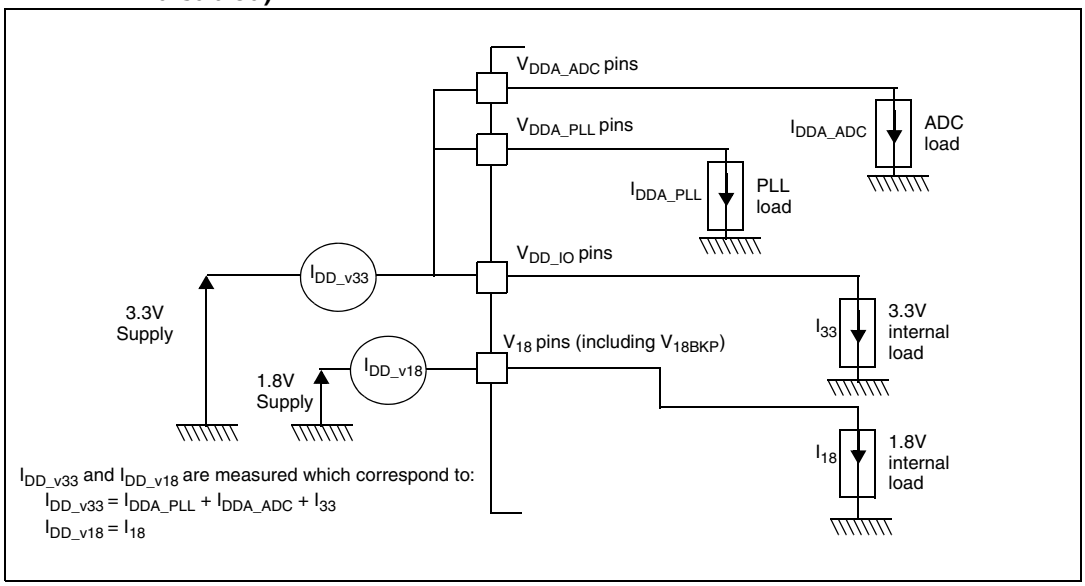


Figure 13. Power consumption measurements in power scheme 2 (regulators disabled)



6.3.4 Supply current characteristics

The current consumption is measured as described in *Figure 12 on page 30* and *Figure 13 on page 30*.

Subject to general operating conditions for V_{DD_IO}, and T_A

Maximum power consumption

For the measurements in *Table 13* and *Table 14*, the MCU is placed under the following conditions:

- All I/O pins are configured in output push-pull 0
- All peripherals are disabled except if explicitly mentioned.
- Embedded Regulators are used to provide 1.8 V (except if explicitly mentioned).

Table 13. Maximum power consumption in RUN and WFI modes

Symbol	Parameter	Conditions (1)		Typ (2)	Max (3)	Unit
I_{DD}	Supply current in RUN mode	External Clock with PLL multiplication, code running from RAM, all peripherals enabled in the MRCC_PLCKEN register: f_{HCLK}=60 MHz, f_{PCLK}=30 MHz Single supply scheme see *Figure 12* / *Figure 14*	3.3V and 5V range	80	90	mA
	Supply current in WFI mode	External Clock, code running from RAM: f_{HCLK}=60 MHz, f_{PCLK}=30 MHz Single supply scheme see *Figure 12*./ *Figure 14* Parameter setting BURST=1, WFI_FLASHEN=1	3.3V and 5V range	62	67	mA

1. The conditions for these consumption measurements are described at the beginning of *Section 6.3.4*.
2. Typical data are based on T_A=25°C, V_{DD_IO}=3.3V or 5.0V and V_{18}=1.8V unless otherwise specified.
3. Data based on product characterisation, tested in production at V_{DD_IO} max and V_{18} max (1.95V in dual supply mode or regulator output value in single supply mode) and T_A max.

Typical power consumption

The following measurement conditions apply to *Table 15*, *Table 16* and *Table 17*.

In RUN mode:

- Program is executed from Flash (except if especially mentioned). The program consists of an infinite loop. When f_{HCLK} > 32 MHz, burst mode is activated.
- A standard 4 MHz crystal source is used.
- In all cases the PLL is used to multiply the frequency.
- All measurements are done in the single supply scheme with internal regulators used (see *Figure 12*)

In WFI Mode:

- In WFI Mode the measurement conditions are similar to RUN mode (OSC4M and PLL enabled). In addition, the Flash can be disabled depending on burst mode activation:
  - For AHB frequencies greater than 32 MHz, burst mode is activated and the Flash is kept enabled by setting the WFI_FLASH_EN bit (this bit cannot be reset when burst mode is activated).
  - For AHB frequencies less than or equal to 32 MHz, burst mode is deactivated, WFI_FLASH_EN is reset and the LP_PARAM14 bit is set (Flash is disabled in WFI mode).

In SLOW mode:

- The same program as in RUN mode is executed from Flash. The CPU is clocked by the FREEOSC, OSC4M, LPOSC or OSC32K. Only EXTIT peripheral is enabled in the MRCC_PCLKEN register.

In SLOW-WFI mode:

- In SLOW-WFI, the measurement conditions are similar to SLOW mode (CPU clocked by a low frequency clock). In addition, the LP_PARAM14 bit is set (FLASH is OFF). The WFI routine itself is executed from SRAM (it is not allowed to execute a WFI from the internal FLASH)

In STOP mode:

- Several measurements are given: in the single supply scheme with internal regulators used (see *Figure 12*): and in the dual supply scheme (see *Figure 13*).

In STANDBY mode:

- Three measurements are given:
  - The RTC is disabled, only the consumption of the LPVREG and RSM remain (almost no leakage currents)
  - The RTC is running, clocked by a standard 32.768 kHz crystal.
  - The RTC is running, clocked by the internal Low Power RC oscillator (LPOSC)
- STANDBY mode is only supported in the single supply scheme (see *Figure 12*)

Table 16. Dual supply supply typical power consumption in Run, WFI, Slow and Slow-WFI modes

To calculate the power consumption in Dual supply mode, refer to the values given in *Table 15*. and consider that this consumption is split as follows:

$I_{DD(single\ supply)} \sim I_{DD(dual\ supply)} = I_{DD\_V18} + I_{DD(VDD\_IO)}$

For 3.3V range: $I_{DD(VDD\_IO)}$ ~ 1 to 2 mA

For 5V range: $I_{DD(VDD\_IO)}$ ~ 2 to 3 mA

Therefore most of the consumption is sunk on the V_{18} power supply

This formula does not apply in STOP and STANDBY modes, refer to *Table 17*.

Subject to general operating conditions for V_{DD_IO}, and T_A

Table 17. Typical power consumption in STOP and STANDBY modes

Symbol	Parameter	Conditions		3.3V Typ(1)	5V Typ(2)	Unit
I_{DD}(3)	Supply current in STOP mode(4)	LP_PARAM bits: ALL OFF(5)		12	15	µA
		LP_PARAM bits : MVREG ON, OSC4M OFF, FLASH OFF(6)		130	135	
		LP_PARAM bits: MVREG ON, OSC4M ON , FLASH OFF(6)		1950	1930	
		LP_PARAM bits: MVREG ON, OSC4M OFF, FLASH ON (6)		630	635	
		LP_PARAM bits: MVREG ON, OSC4M ON, FLASH ON (6)		2435	2425	
	Supply current in STOP mode(7)	LPPARAM bits: ALL OFF, with V_{18}=1.8 V	I_{DD_V18} I_{DD_V33}	5 <1	5 <1	µA
		LP_PARAM bits: OSC4M ON, FLASH OFF	I_{DD_V18} I_{DD_V33}	410 1475	410 1435	
		LP_PARAM bits: OSC4M OFF, FLASH ON	I_{DD_V18} I_{DD_V33}	550 <1	550 1	
		LP_PARAM bits: OSC4M ON, FLASH ON	I_{DD_V18} I_{DD_V33}	910 1475	910 1445	
	Supply current in STANDBY mode(4)	RTC OFF		11	14	µA
		RTC ON clocked by OSC32K		14	18	

1. Typical data are based on T_A=25°C, V_{DD_IO}=3.3 V and V_{18}=1.8 V unless otherwise indicated in the table.
2. Typical data are based on T_A=25°C, V_{DD_IO}=5.0 V and V_{18}=1.8 V unless otherwise indicated in the table.
3. The conditions for these consumption measurements are described at the beginning of *Section 6.3.4 on page 36*.
4. Single supply scheme see *Figure 12*.
5. In this mode, the whole digital circuitry is powered internally by the LPVREG at approximately 1.4 V, which significantly reduces the leakage currents.
6. In this mode, the whole digital circuitry is powered internally by the MVREG at 1.8 V.
7. Dual supply scheme see *Figure 13*.

4/8 MHz crystal / ceramic resonator oscillator (XT1/XT2)

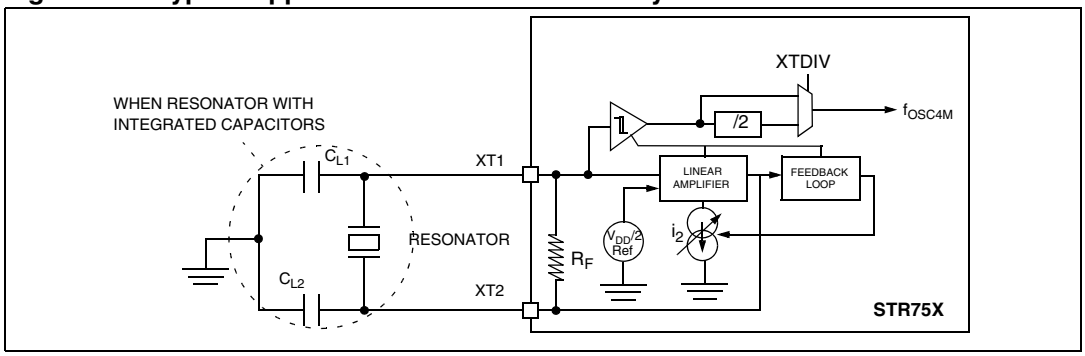
The STR750 system clock or the input of the PLL can be supplied by a OSC4M which is a 4 MHz clock generated from a 4 MHz or 8 MHz crystal or ceramic resonator. If using an 8 MHz oscillator, software set the XTDIV bit to enable a divider by 2 and generate a 4 MHz OSC4M clock. All the information given in this paragraph are based on product characterisation with specified typical external components. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and start-up stabilization time. Refer to the crystal/ceramic resonator manufacturer for more details (frequency, package, accuracy...).

Table 22. 4/8 MHz crystal / ceramic resonator oscillator (XT1/XT2)(1)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{OSC4M}	Oscillator frequency	4 MHz Crystal/Resonator Oscillator connected on XT1/XT2 XTDIV=0 or 8 MHz Crystal/Resonator Oscillator connected on XT1/XT2 XTDIV=1		4		MHz
R_F	Feedback resistor		200	240	270	kΩ
C_{L1}(2) C_{L2}	Recommended load capacitance versus equivalent serial resistance of the crystal or ceramic resonator (R_S)(3)	R_S=200Ω			60	pF
i_2	XT2 driving current	V_{DD_IO}=3.3 V or 5.0 V		425		µA
$t_{SU(OSC4M)}$(4)	Startup time at V_{DD_IO} power-up			1		ms

1. Resonator characteristics given by the crystal/ceramic resonator manufacturer.
2. For C_{L1} and C_{L2} it is recommended to use high-quality ceramic capacitors in the 5-pF to 25-pF range (typ.) designed for high-frequency applications and selected to match the requirements of the crystal or resonator. C_{L1} and C_{L2}, are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of C_{L1} and C_{L2}. PCB and MCU pin capacitance must be included when sizing C_{L1} and C_{L2} (10 pF can be used as a rough estimate of the combined pin and board capacitance).
3. The relatively low value of the RF resistor offers a good protection against issues resulting from use in a humid environment, due to the induced leakage and the bias condition change. However, it is recommended to take this point into account if the MCU is used in tough humidity conditions.
4. $t_{SU(OSC4M)}$ is the typical start-up time measured from the moment V_{DD_IO} is powered (with a quick V_{DD_IO} ramp-up from 0 to 3.3V (<50µs) to a stabilized 4MHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal/ceramic resonator manufacturer.

Figure 21. Typical application with a 4 or 8 MHz crystal or ceramic resonator



6.3.7 EMC characteristics

Susceptibility tests are performed on a sample basis during product characterization.

Functional EMS (electro magnetic susceptibility)

Based on a simple running application on the product (toggling 2 LEDs through I/O ports), the product is stressed by two electro magnetic events until a failure occurs (indicated by the LEDs).

- **ESD**: Electro-Static Discharge (positive and negative) is applied on all pins of the device until a functional disturbance occurs. This test conforms with the IEC 1000-4-2 standard.
- **FTB**: A Burst of Fast Transient voltage (positive and negative) is applied to V_{DD} and V_{SS} through a 100pF capacitor, until a functional disturbance occurs. This test conforms with the IEC 1000-4-4 standard.

A device reset allows normal operations to be resumed. The test results are given in the table below based on the EMS levels and classes defined in application note AN1709.

Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

Software recommendations:

The software flowchart must include the management of runaway conditions such as:

- Corrupted program counter
- Unexpected reset
- Critical Data corruption (control registers...)

Prequalification trials:

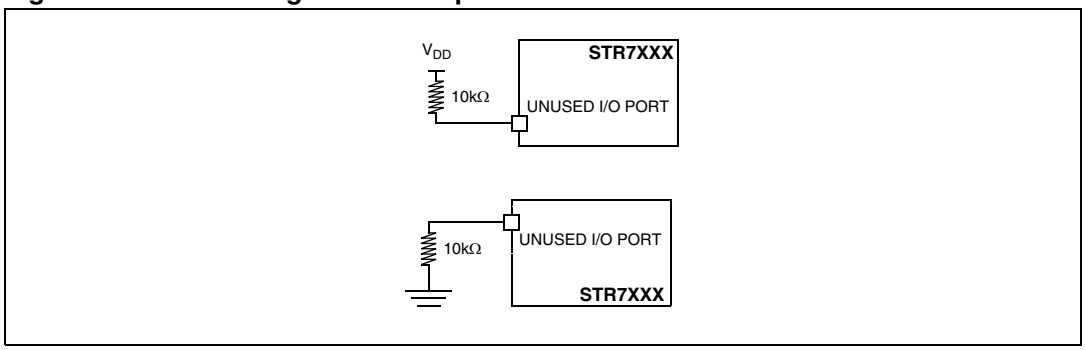
Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the RESET pin or the Oscillator pins for 1 second.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behaviour is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

Table 28. EMC characteristics

Symbol	Parameter	Conditions	Level/ Class
V_{FESD}	Voltage limits to be applied on any I/O pin to induce a functional disturbance	V_{DD_IO}=3.3 V or 5 V, T_A=+25° C, f_{CK_SYS}=32 MHz conforms to IEC 1000-4-2	Class A
V_{EFTB}	Fast transient voltage burst limits to be applied through 100pF on V_{DD} and V_{SS} pins to induce a functional disturbance	V_{DD_IO}=3.3 V or 5 V, T_A=+25° C, f_{CK_SYS}=32 MHz conforms to IEC 1000-4-4	Class A

Figure 25. Connecting unused I/O pins



Output driving current

The GP I/Os have different drive capabilities:

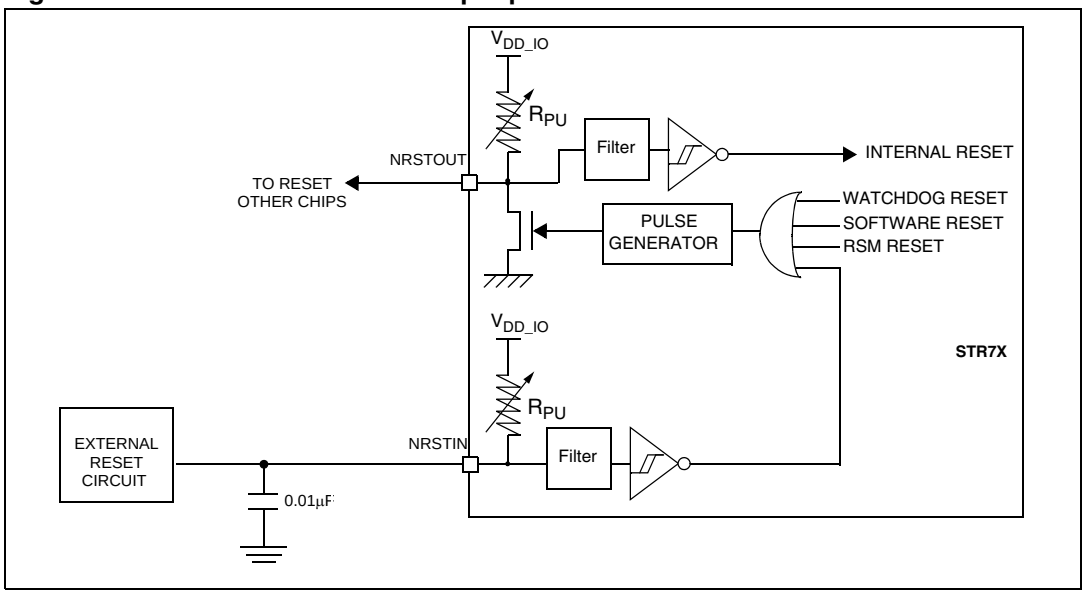
- O2 outputs can sink or source up to +/-2 mA.
- O4 outputs can sink or source up to +/-4 mA.
- outputs can sink or source up to +/-8 mA or can sink +20 mA (with a relaxed V_{OL}).

In the application, the user must limit the number of I/O pins which can drive current to respect the absolute maximum rating specified in *Section 6.2.2* :

- The sum of the current sourced by all the I/Os on $V_{DD\_IO,}$ plus the maximum RUN consumption of the MCU sourced on $V_{DD\_IO,}$ can not exceed the absolute maximum rating IV_{DD_IO}.
- The sum of the current sunk by all the I/Os on V_{SS_IO} plus the maximum RUN consumption of the MCU sunk on V_{SS_IO} can not exceed the absolute maximum rating IV_{SS_IO}.

Subject to general operating conditions for V_{DD_IO} and T_A unless otherwise specified.

Figure 27. Recommended NRSTIN pin protection



1. The user must ensure that the level on the NRSTIN pin can go below the $V_{IL(NRSTIN)}$ max. level specified in *NRSTIN and NRSTOUT pins on page 58*. Otherwise the reset will not be taken into account internally.

Figure 28. SPI configuration - master mode, single transfer

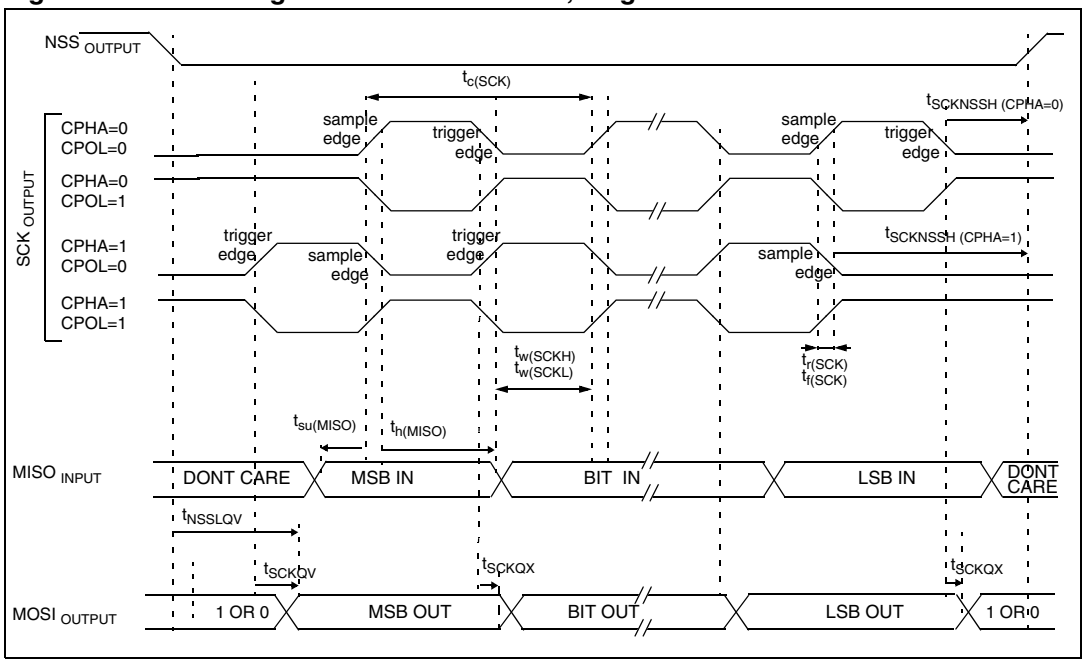


Figure 29. SPI configuration - master mode, continuous transfer, CPHA=0

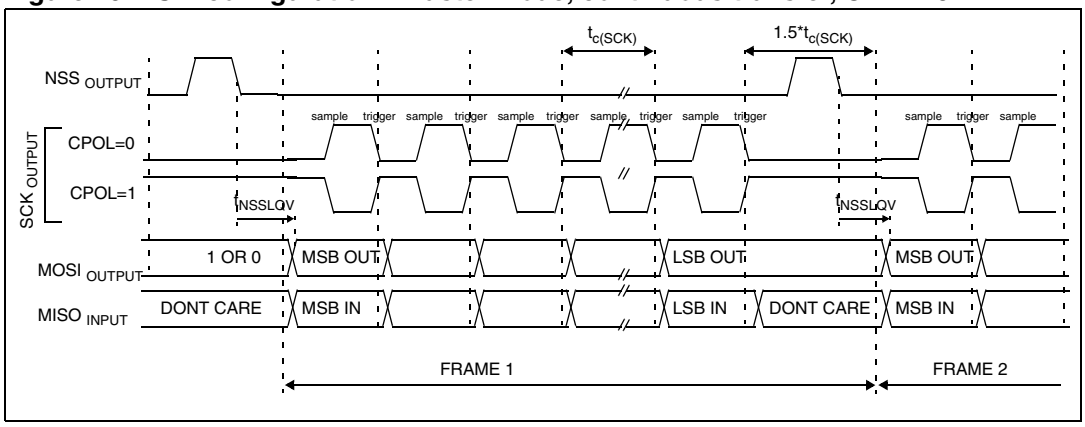
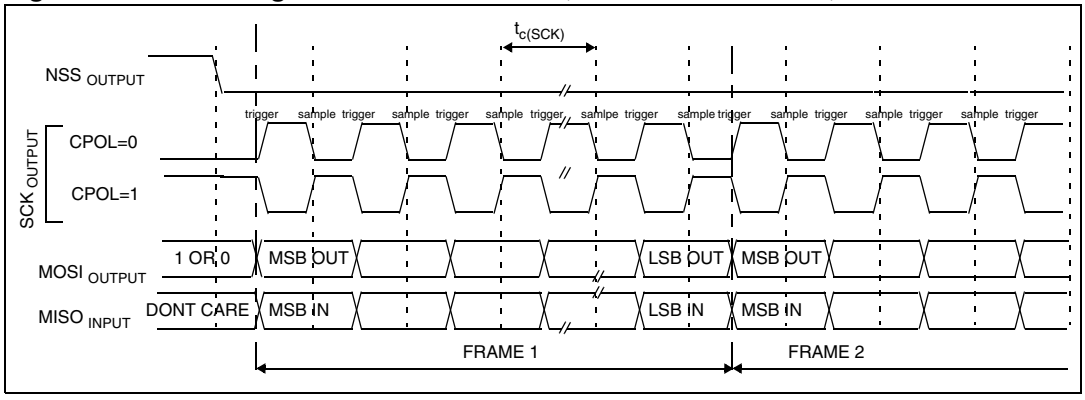


Figure 30. SPI configuration - master mode, continuous transfer, CPHA=1



SSP synchronous serial peripheral in slave mode (SPI or TI mode)

Subject to general operating conditions with $C_L \approx 45$ pF

Table 39. SSP slave mode characteristics(1)

Symbol	Parameter	Conditions		Min	Max	Unit
f_{SCK}	SPI clock frequency		SSP0		2.66 MHz (f_{PLCK}/12)	MHz
			SSP1			
$t_{su(NSS)}$	NSS input setup time w.r.t SCK first edge		SSP0	0		ns
			SSP1	0		
$t_{h(NSS)}$	NSS input hold time w.r.t SCK last edge		SSP0	t_{PCLK}+15ns		
			SSP1	t_{PCLK}+15ns		
t_{NSSLQV}	NSS low to Data Output MISO valid time		SSP0	$2t_{PCLK}$	$3t_{PCLK}$+30 ns	
			SSP1	$2t_{PCLK}$	$3t_{PCLK}$+30 ns	
t_{NSSLQZ}	NSS low to Data Output MISO invalid time		SSP0	$2t_{PCLK}$	$3t_{PCLK}$+15 ns	
			SSP1	$2t_{PCLK}$	$3t_{PCLK}$+15 ns	
t_{SCKQV}	SCK trigger edge to data output MISO valid time		SSP0		15	
			SSP1		30	
t_{SCKQX}	SCK trigger edge to data output MISO invalid time		SSP0	$2t_{PCLK}$		
			SSP1	$2t_{PCLK}$		
$t_{su(MOSI)}$	MOSI setup time w.r.t SCK sampling edge		SSP0	0		
			SSP1	0		
$t_{h(MOSI)}$	MOSI hold time w.r.t SCK sampling edge		SSP0	$3t_{PCLK}$+15 ns		
			SSP1	$3t_{PCLK}$+15 ns		

1. Data based on characterisation results, not tested in production.

Figure 33. SPI configuration, slave mode with CPHA=0, single transfer

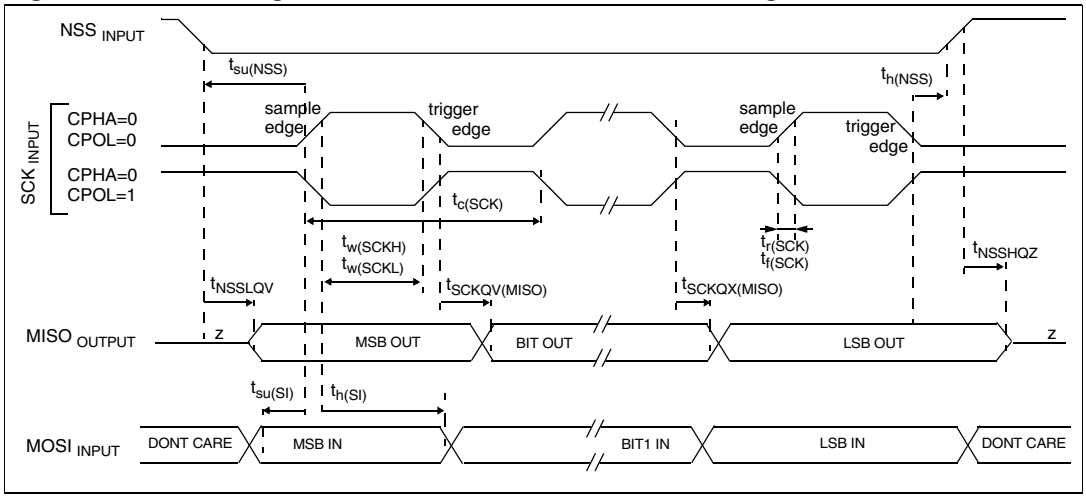


Figure 37. TI configuration - slave mode, single transfer

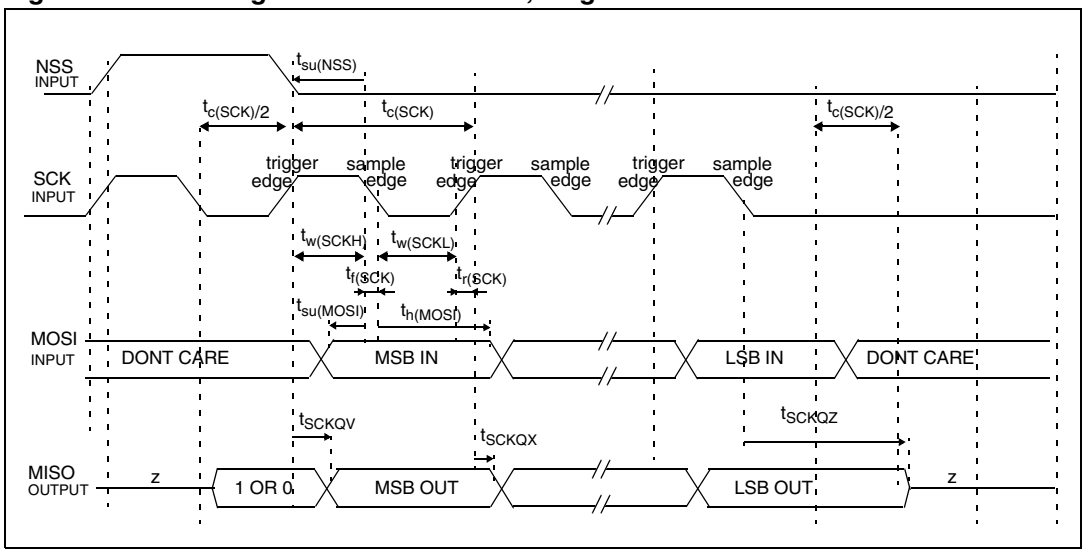


Figure 38. TI configuration - slave mode, continuous transfer

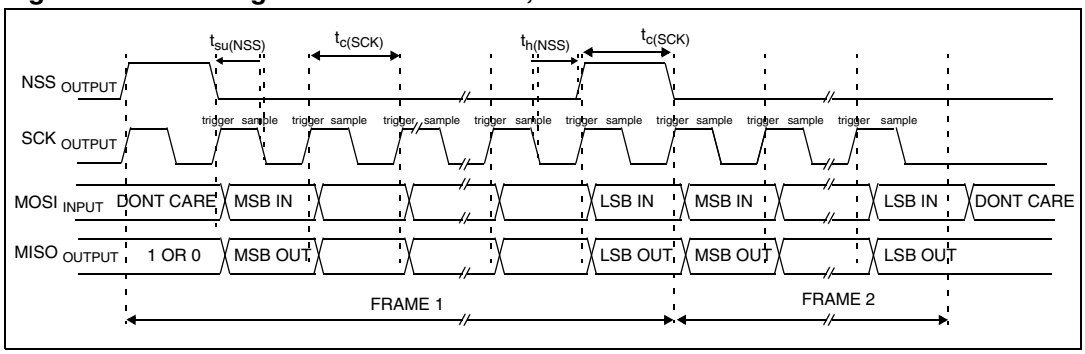
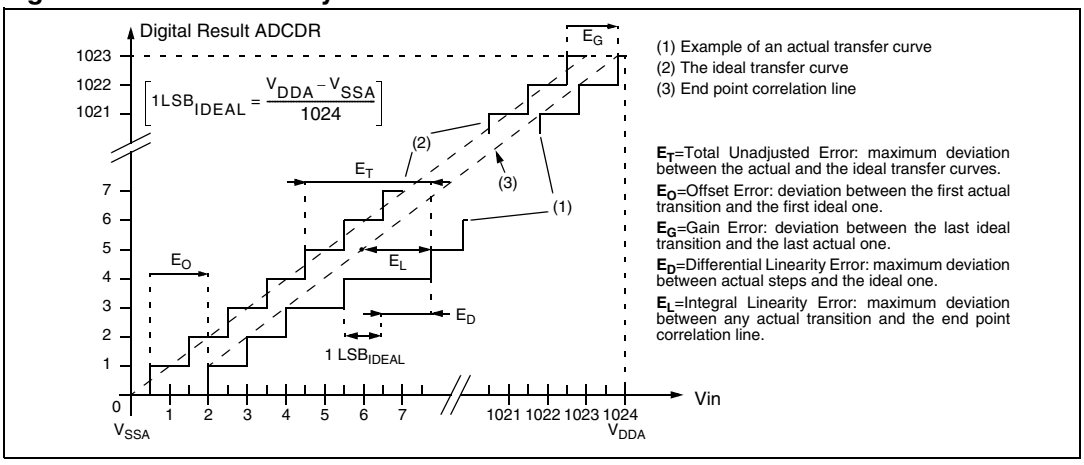


Table 47. ADC accuracy

ADC accuracy with f_{CK_SYS} = 20 MHz, f_{ADC}=8 MHz, R_{AIN} < 10 kΩ This assumes that the ADC is calibrated(1)					
Symbol	**Parameter**	**Conditions**	**Typ**	**Max**	**Unit**
$\|E_T\|$	Total unadjusted error (2) (3)	V_{DDA_ADC}=3.3 V	1	1.2	LSB
		V_{DDA_ADC}=5.0 V	1	1.2	
$\|E_O\|$	Offset error(2) (3)	V_{DDA_ADC}=3.3 V	0.15	0.5	
		V_{DDA_ADC}=5.0 V	0.15	0.5	
E_G	Gain Error (2) (3)	V_{DDA_ADC}=3.3 V	-0.8	-0.2	
		V_{DDA_ADC}=5.0 V	-0.8	-0.2	
$\|E_D\|$	Differential linearity error(2) (3)	V_{DDA_ADC}=3.3 V	0.7	0.9	
		V_{DDA_ADC}=5.0 V	0.7	0.9	
$\|E_L\|$	Integral linearity error (2) (3)	V_{DDA_ADC}=3.3 V	0.6	0.8	
		V_{DDA_ADC}=5.0 V	0.6	0.8	

1. Calibration is needed once after each power-up.
2. Refer to *ADC accuracy vs. negative injection current on page 73*
3. ADC Accuracy vs. MCO (Main Clock Output): the ADC accuracy can be significantly degraded when activating the MCO on pin P0.01 while converting an analog channel (especially those which are close to the MCO pin). To avoid this, when an ADC conversion is launched, it is strongly recommended to disable the MCO.

Figure 44. ADC accuracy characteristics



7.2 Thermal characteristics

The maximum chip junction temperature (T_{Jmax}) must never exceed the values given in *Table 10: General operating conditions on page 34*.

The maximum chip-junction temperature, T_{Jmax}, in degrees Celsius, may be calculated using the following equation:

$$T_{Jmax} = T_{Amax} + (P_{Dmax} \times \Theta_{JA})$$

Where:

- T_{Amax} is the maximum Ambient Temperature in °C,
- Θ_{JA} is the Package Junction-to-Ambient Thermal Resistance, in ° C/W,
- P_{Dmax} is the sum of P_{INTmax} and $P_{I/Omax}$ ($P_{Dmax} = P_{INTmax} + P_{I/Omax}$),
- P_{INTmax} is the product of I_{DD} and V_{DD}, expressed in Watts. This is the maximum chip internal power.
- $P_{I/Omax}$ represents the maximum Power Dissipation on Output Pins.
  Where:
  $P_{I/Omax} = \Sigma (V_{OL}*I_{OL}) + \Sigma((V_{DD}-V_{OH})*I_{OH})$,
  taking into account the actual V_{OL} / I_{OL} and V_{OH} / I_{OH} of the I/Os at low and high level in the application.

Table 48. Thermal characteristics(1)

Symbol	Parameter	Value	Unit
Θ_{JA}	**Thermal Resistance Junction-Ambient** LQFP 100 - 14 x 14 mm / 0.5 mm pitch	46	°C/W
Θ_{JA}	**Thermal Resistance Junction-Ambient** LQFP 64 - 10 x 10 mm / 0.5 mm pitch	45	°C/W
Θ_{JA}	**Thermal Resistance Junction-Ambient** LFBGA 64 - 8 x 8 x 1.7mm	58	°C/W
Θ_{JA}	**Thermal Resistance Junction-Ambient** LFBGA 100 - 10 x 10 x 1.7mm	41	°C/W

1. Thermal resistances are based on JEDEC JESD51-2 with 4-layer PCB in a natural convection environment.

7.2.1 Reference document

JESD51-2 Integrated Circuits Thermal Test Method Environment Conditions - Natural Convection (Still Air). Available from www.jedec.org

8 Order codes

Table 49. Order codes

Order code	Flash Prog. Memory (Bank 0) Kbytes	Package	CAN Periph	USB Periph	Nominal Temp. Range (T_A)
STR750FV0T6	64	LQFP100 14x14	Yes	Yes	-40 to +85°C
STR750FV1T6	128				
STR750FV2T6	256				
STR750FV0H6	64	LFBGA100 10x10			
STR750FV1H6	128				
STR750FV2H6	256				
STR751FR0T6	64	LQFP64 10x10	-	Yes	-40 to +85°C
STR751FR1T6	128				
STR751FR2T6	256				
STR751FR0H6	64	LFBGA64 8x8			
STR751FR1H6	128				
STR751FR2H6	256				
STR752FR0T6	64	LQFP64 10x10	Yes	-	-40 to +85°C
STR752FR1T6	128				
STR752FR2T6	256				
STR752FR0H6	64	LFBGA64 8x8			
STR752FR1H6	128				
STR752FR2H6	256				
STR752FR0T7	64	LQFP64 10x10	Yes	-	-40 to +105°C
STR752FR1T7	128				
STR752FR2T7	256				
STR752FR0H7	64	LFBGA64 8x8			
STR752FR1H7	128				
STR752FR2H7	256				
STR755FR0T6	64	LQFP64 10x10	-	-	-40 to +85°C
STR755FR1T6	128				
STR755FR2T6	256				
STR755FR0H6	64	LFBGA64 8x8			
STR755FR1H6	128				
STR755FR2H6	256				